优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

$V_{(BR)DSS}$	$R_{DS(on)\ max}$	I_D T_A = +25°C
-30V	65mΩ @ V_{GS} = -10V	-4.4A
	115mΩ @ V_{GS} = -4.5V	-3.2A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- Analog Switch
- Load Switch
- Boost Switch

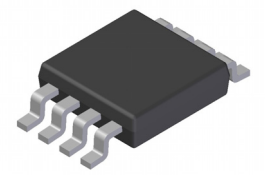
Features

- Dual P-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage

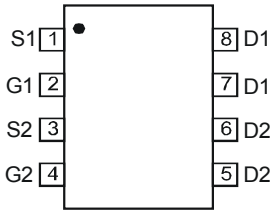
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.072g (approximate)

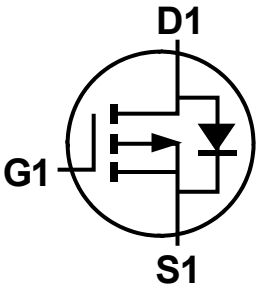
SO-8



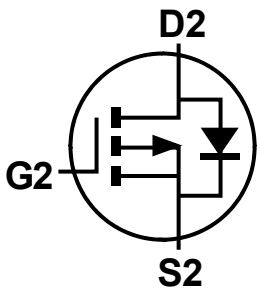
TOP VIEW



TOP VIEW
Internal Schematic



P-Channel MOSFET



P-Channel MOSFET

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Drain Current (Note 5)	Steady State	T_A = +25°C T_A = +70°C	I_D	-4.4 -3.3	A
Pulsed Drain Current (Note 6)			I_{DM}	-15	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	1.8	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	70	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	μA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-1	1.7	-2.1	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	— —	56 98	65 115	mΩ	V_{GS} = -10V, I_D = -5.0A V_{GS} = -4.5V, I_D = -4.0A
Forward Transconductance	g_{fs}	—	5.2	—	S	V_{DS} = -10V, I_D = -5.0A
Diode Forward Voltage (Note 7)	V_{SD}	-0.5	—	-1.2	V	V_{GS} = 0V, I_S = -2.6A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	336	—	pF	V_{DS} = -25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	70	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	49	—	pF	
Gate Resistance	R_G	—	4.6	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_g	—	4.0 7.8	—	nC	V_{DS} = -15V, V_{GS} = -4.5V,I_D = -5.0A V_{DS} = -15V, V_{GS} = -10V,I_D = -5.0A
Gate-Source Charge	Q_{gs}	—	1.0	—		V_{DS} = -15V, V_{GS} = -4.5V,I_D = -5.0A
Gate-Drain Charge	Q_{gd}	—	2.5	—		V_{DS} = -15V, V_{GS} = -4.5V,I_D = -5.0A
Turn-On Delay Time	$t_{d(on)}$	—	6.0	—	ns	V_{DS} = -15V, V_{GS} = -10V, I_D = -1A, R_G = 6.0Ω
Rise Time	t_r	—	5.0	—		
Turn-Off Delay Time	$t_{d(off)}$	—	17.6	—		
Fall Time	t_f	—	9.5	—		

Notes: 5. Device mounted on 2 oz. 1" x 1" Copper pads on 2" x 2" FR-4 PCB.
6. Pulse width ≤10μS, Duty Cycle ≤1%.
7. Short duration pulse test used to minimize self-heating effect.

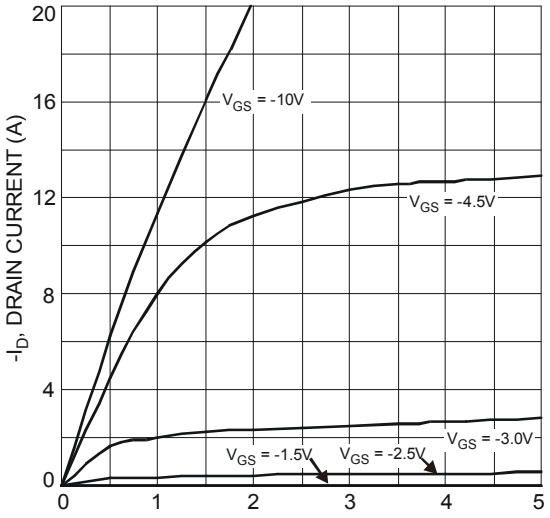


Fig. 1 Typical Output Characteristics

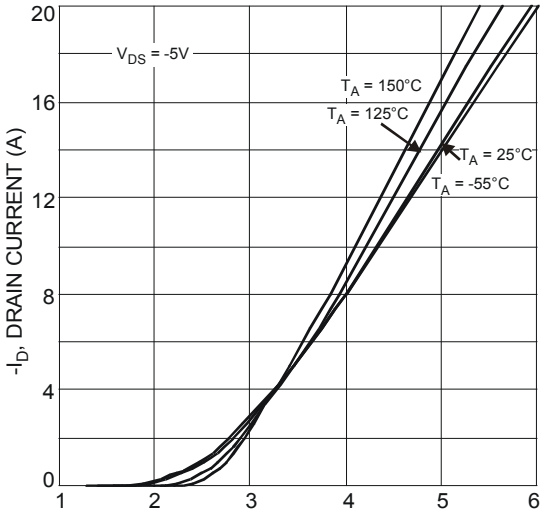


Fig. 2 Typical Transfer Characteristics

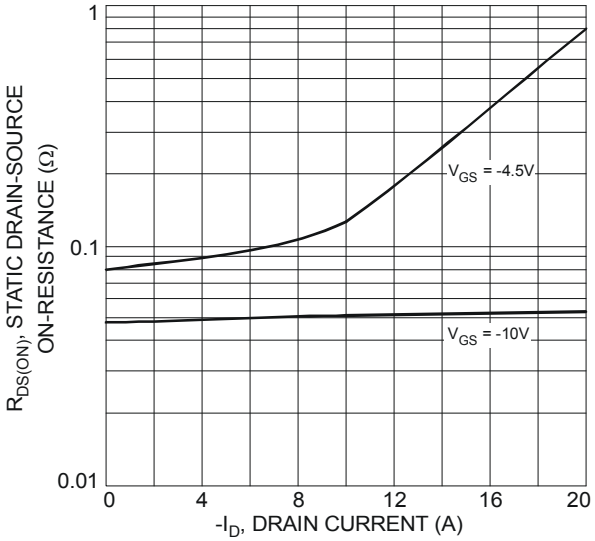


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

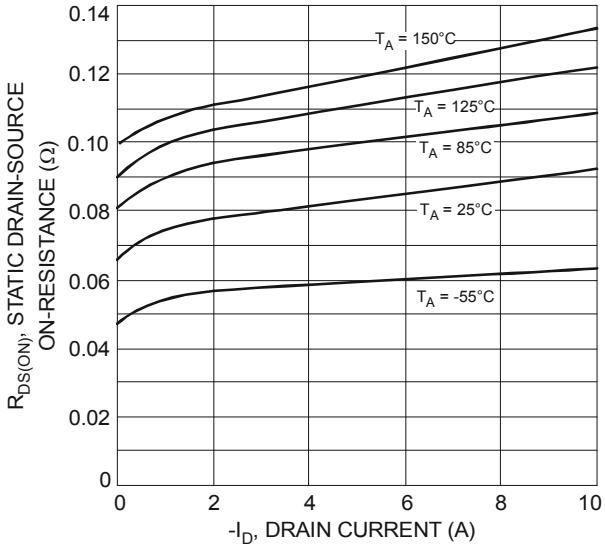


Fig. 4 Typical On-Resistance
vs. Drain Current and Temperature

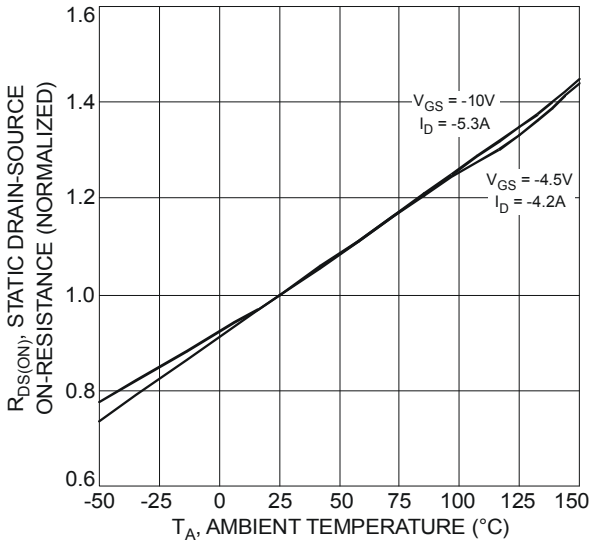


Fig. 5 On-Resistance Variation with Temperature

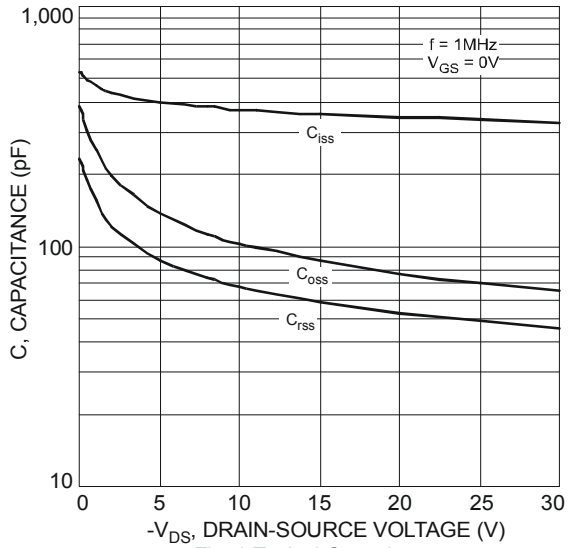


Fig. 6 Typical Capacitance

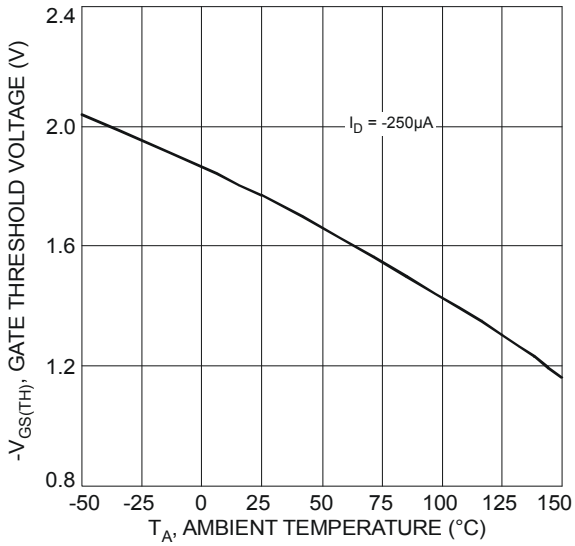


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

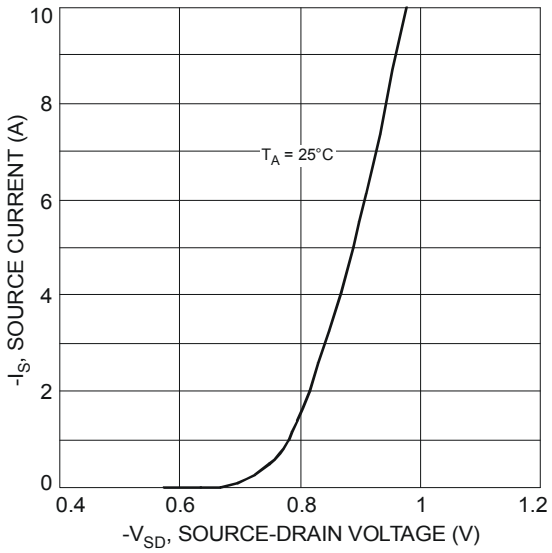
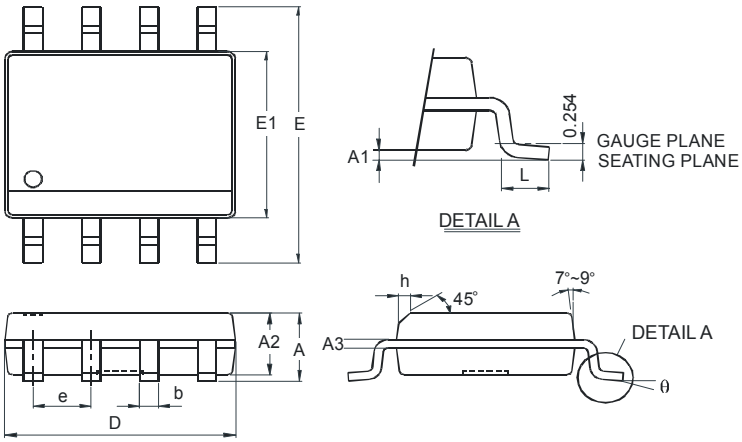


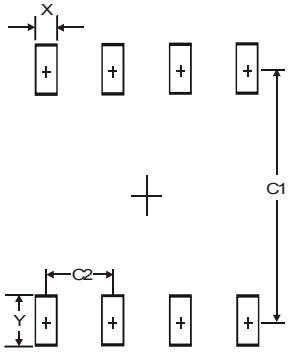
Fig. 8 Diode Forward Voltage vs. Current

Package Outline Dimensions



SO-8		
Dim	**Min**	**Max**
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27